Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

H882

APPLICATIONS

Audio Frequency Power Amplifier , Switching Power Amplifier.

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature····· 150℃

P_C——Collector Dissipation (T_c=25℃) ····· 10W

P_C——Collector Dissipation (T_A=25℃) ····· 1W

V_{CBO}——Collector-Base Voltage····· 40V

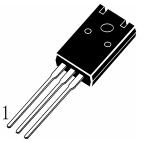
V_{CEO}——Collector-Emitter Voltage····· 30V

V_{EBO}——Emitter-Base Voltage····· 5V

I_C——Collector Current (DC) ·····3A

Ib——Base Current (DC) ·····0.6A

TO-126ML



1—Emitter，E
2—Collector，C
3—Base，B

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector-Base Cutoff Current			1	μA	V_{CB}=30V, I_E=0
I_{EBO}	Emitter- Base Cutoff Current			1	μA	V_{EB}=5V, I_C=0
h_{FE}	DC Current Gain	60		400		V_{CE}=-2V, I_C=1A
$V_{CE\ (sat)}$	Collector- Emitter Saturation Voltage		0.3	0.5	V	I_C=2A, I_B=-0.2A
$V_{BE\ (sat)}$	Base -Emitter Saturation Voltage		1.0	2.0	V	I_C=2A, I_B=0.2A
C_{ob}	Output Capacitance		45		pF	V_{CB}=10V，I_E=0，f=1MHz
f_T	Current Gain-Bandwidth Product		90		MHz	V_{CE}=5V，I_E=0.1A

h_{FE} Classification

R	O	Y	G
60—120	100—200	160—320	200—400

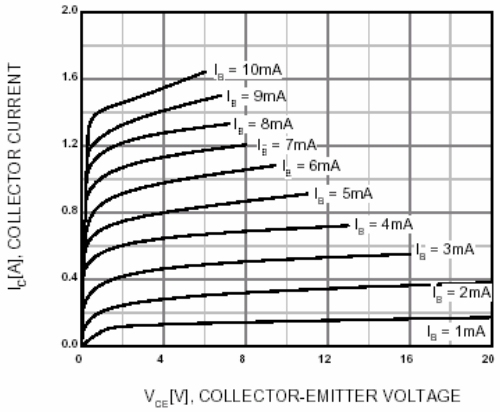


Figure 1. Static Characteristic

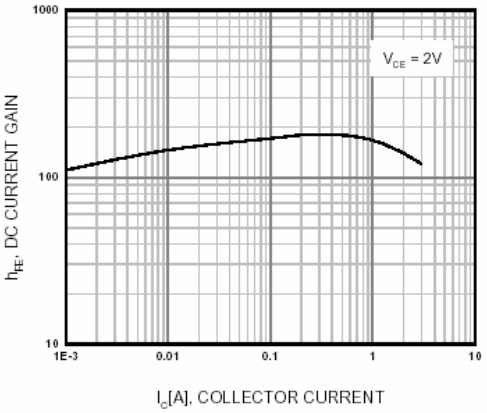


Figure 2. DC current Gain

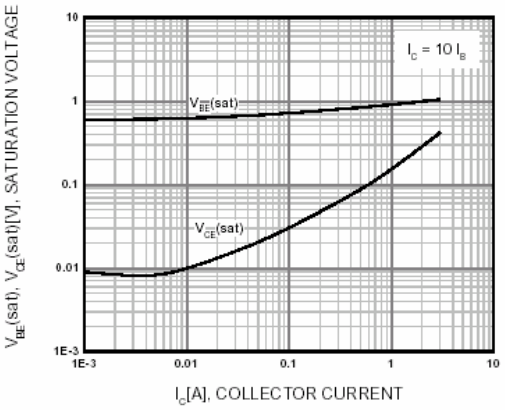


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

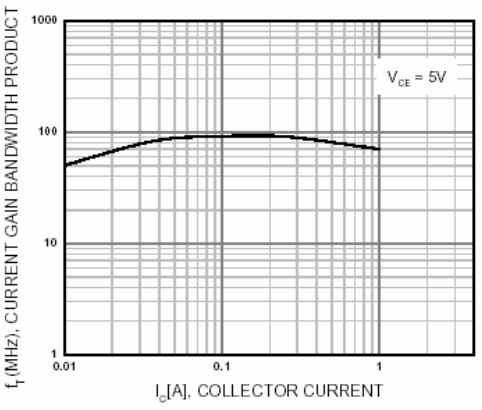


Figure 4. Current Gain Bandwidth Product

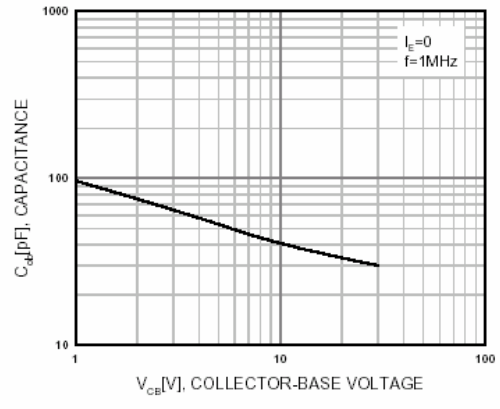


Figure 5. Collector Output Capacitance

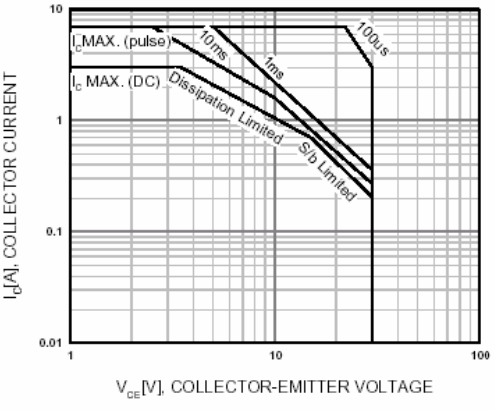


Figure 6. Safe Operating Area

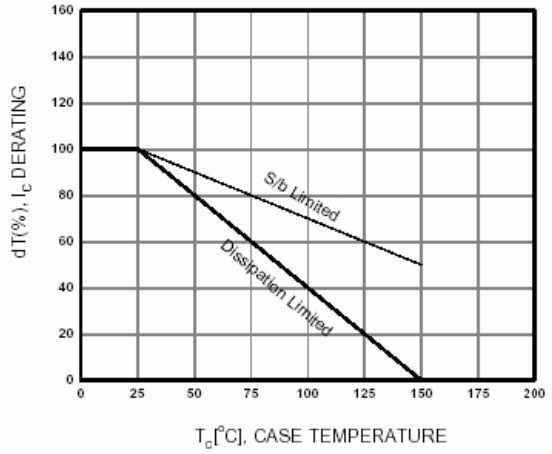


Figure 7. Derating Curve Of Safe Operating Areas

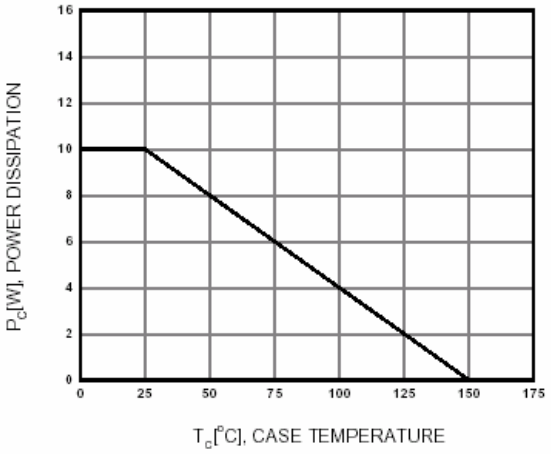


Figure 8. Power Derating